ABSTRACT OF THE DISLOSURE

Disclosed is a solid state image pickup device including a Si substrate, a conductive pattern such as transfer-accumulation electrodes and a buffer wiring formed above the Si substrate, an insulating film provided above the Si substrate in the state of covering the conductive pattern, and a shunt wiring composed of a metallic pattern formed above the insulating film in the state of being connected to the buffer wiring via a contact window formed in the insulating film. The portion of the shunt wiring in the vicinity of the bottom surface of the contact window contains at least one of silicon metal oxide or silicon metal nitride. The solid state image pickup device and a method of fabricating the same make it possible to suppress a rise in the contact resistance attendant on a heat treatment in a later step, in a structure in which various wirings and a light shielding film using a metallic material and a conductive pattern such as a Si substrate and a Si-containing electrode or wiring are brought into contact with each other, to improve propagation characteristics of various signals, and to contribute to provision of an image pickup device with a higher speed, a larger size, a higher image quality, etc.